



PTO/SB/08A/B (09-06)

Approved for use through 03/31/2007. OMB 0651-0031

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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/774,890
				Filing Date	February 9, 2004
				First Named Inventor	Fitzgerald
				Art Unit	2818
				Examiner Name	D. A. Le
				Attorney Docket Number	ASC-049C1
Sheet	1	of	1		

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
DL	A353	US-6,881,630	04-19-2005	Song et al.	

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
DL	C338	Office action in Ex Parte Reexamination of U.S. Patent No. 6,703,688, March 12, 2007.	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	DL	Date Considered	5/2007
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A291	US-6,861,318-A1	03-01-2005	Murthy et al.	
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A339	US-20050130454-A1	06-16-2005	Murthy et al.	

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<input checked="" type="checkbox"/>	A351	US-20060009001-A1	01-12-2006	Huang et al.	
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FOREIGN PATENT DOCUMENTS							
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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)					
	B49	EP-0390661		10-03-1990			
	B50	JP-4-74415		03-09-1992			
	B51	JP-2000-031491		01-28-2000			✓
	B52	JP-2002-324765		11-08-2002		abstract only	✓

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. CITE NO.: Those application(s) which are marked with an asterisk (*) next to the Cite No. are not supplied (under 37 CFR 1.98(a)(2)(iii)) because that application was filed after June 30, 2003 or is available in the IFW. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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	C177	AmberWave Systems Corporation's Second Supplemental Responses to Intel's Third Set of Interrogatories, U.S.D.C., District of Delaware, C.A. No. 05-301-KAJ (July 12, 2006).		
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C195	Cowern et al., "Diffusion in Strained Si(Ge)," 72 Physical Review Letters 2585 (1994).
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